

# MA4X174

## Silicon planar type

For small power rectification and surge absorption

### ■ Features

- Two isolated elements contained in one package, allowing high-density mounting
- High voltage ( $V_R$ : 200 V) rectification is possible

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Repetitive peak reverse voltage	$V_{RRM}$	250	V
Non-repetitive peak forward surge current	$V_{RSM}$	300	V
Output current <sup>*1</sup>	$I_O$	100	mA
Repetitive peak forward current <sup>*1</sup>	$I_{FRM}$	225	mA
Non-repetitive peak forward surge current <sup>*1,2</sup>	$I_{FSM}$	500	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

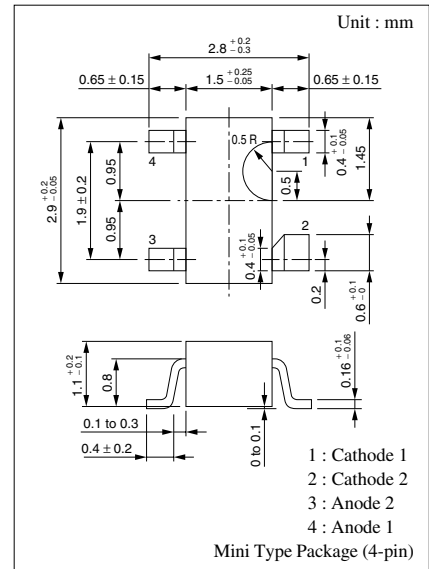
Note) \*1 : Value in single diode used

\*2 :  $t = 1 \text{ s}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200 \text{ V}$			1.0	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 100 \text{ mA}$			1.3	V

Note) 1. Rated input/output frequency: 3 MHz



Marking Symbol: M2Q

Internal Connection

